

IN THE CLAIMS

Please cancel claims 1-10, and in place thereof substitute new claims 11-20 as follows:

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Sub 7
- 11. A method for removing a deposited film inside a chamber which comprises:
providing a hot element in the chamber, the hot element having at least a surface
which comprises platinum;
exhausting said chamber;
heating the hot element;
supplying a cleaning gas into the chamber;
contacting the cleaning gas with the heated hot element to decompose and/or
activate the cleaning gas and generate an activated species therefrom;
allowing the activated species to convert the deposited film into a gaseous
substance; and
removing the gaseous substance from the chamber.- -

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- -12. The method according to claim 11, wherein said chamber comprises a CVD
apparatus and the method further comprises:
heating the hot element;
supplying a material gas to the chamber;
contacting the material gas with the hot element to cause decomposition and/or
activation of the material gas by said hot element; and
forming the deposited film which comprises at least one element from said
material gas on a substrate.- -

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Sub 7
- -13. The method according to claim 11, wherein at least a part of a surface of an
inner structure of said chamber is covered with platinum.- -

- -14. The method according to claim 12, wherein at least a part of the surface of
an inner structure of said chamber is covered with platinum.- -

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- -15. The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), and sulfur hexafluoride (SF_6), and mixtures thereof- -

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- -16. The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine (F_2), chlorine (Cl_2), nitrogen trifluoride (NF_3), carbon tetrafluoride (CF_4), hexafluoroethane (C_2F_6), octafluoropropane (C_3F_8), carbon tetrachloride (CCl_4), pentafluorochloroethane (C_2ClF_5), trifluorochlorine (ClF_3), trifluorochloromethane ($CClF_3$), sulfur hexafluoride (SF_6), and mixtures thereof.- -

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- -17. A CVD apparatus comprising:
a chamber having a material gas inlet and a cleaning gas inlet;
a hot element located in the chamber, the hot element having a surface which comprises platinum;
means for exhausting the chamber;

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a source of material gas coupled to the material gas inlet;
means for heating the hot element to a first temperature sufficient to decompose and/or activate the material gas:
a source of cleaning gas coupled to the cleaning gas inlet; and
means for heating the hot element to a second temperature sufficient to decompose and/or activate the cleaning gas to generate an activated species therefrom which active species is able to convert a film deposited inside said chamber to gaseous substance, which gaseous substance can be removed from the chamber by exhausting the chamber.- -

- -18. The CVD apparatus according to claim 17, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.- -